

ABSTRACT

AN ULTRA-THIN INTEGRATED CHIP AND MANUFACTURE OF THE SAME

A method of fabricating a semiconductor device, the method comprising: forming a substrate;
5 forming a support layer from a first type of material which is not susceptible to an etch
process having a predetermined thickness that is related to a required thickness of the
semiconductor device; forming a device on the support layer; forming at least one layer of
cladding material on the device; forming a plurality of trenches in the layers that extend at
least down to the substrate; applying a film over the cladding material; removing the substrate
10 at least in part using an etching process to separate the device from others on a wafer.

[Figure 2]